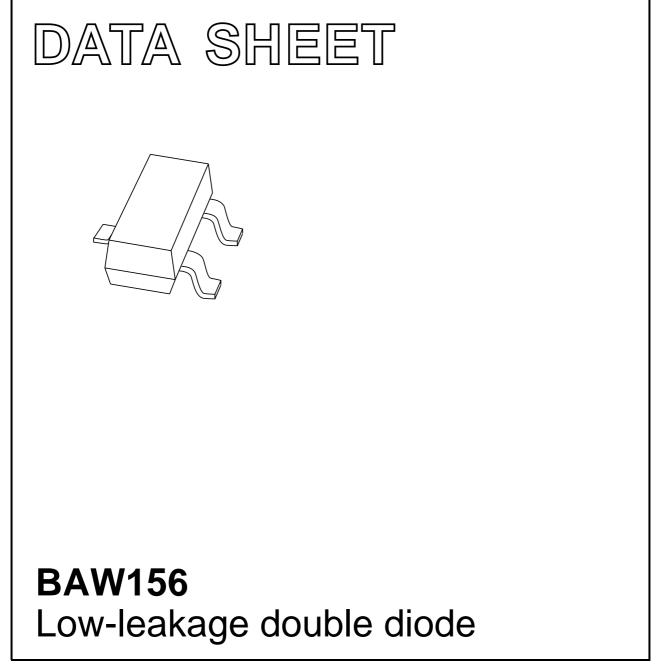
# DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1996 Mar 13 1999 May 11



### FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

### APPLICATION

• Low-leakage current applications in surface mounted circuits.

#### DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small SOT23 plastic SMD package. The diodes are in common anode configuration.

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL           | PARAMETER                           | CONDITIONS   | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|--|------|------|------|
| Per diode        |                                     |  |      |      | •    |
| V <sub>RRM</sub> | repetitive peak reverse voltage     |  | _    | 85   | V    |
| V <sub>R</sub>   | continuous reverse voltage          |  | -    | 75   | V    |
| l <sub>F</sub>   | continuous forward current          | single diode loaded; note 1; see Fig.2                           | -    | 160  | mA   |
|                  |                                     | double diode loaded; note 1; see Fig.2                           | -    | 140  | mA   |
| I <sub>FRM</sub> | repetitive peak forward current     |  | _    | 500  | mA   |
| I <sub>FSM</sub> | non-repetitive peak forward current | square wave; T <sub>j</sub> = 25 °C prior to surge;<br>see Fig.4 |      |      |      |
|                  |                                     | $t_p = 1 \ \mu s$  | _    | 4    | А    |
|                  |                                     | $t_p = 1 ms$   | _    | 1    | А    |
|                  |                                     | t <sub>p</sub> = 1 s   | _    | 0.5  | А    |
| P <sub>tot</sub> | total power dissipation             | $T_{amb} \le 25 \ ^{\circ}C;$ note 1                             | -    | 250  | mW   |
| T <sub>stg</sub> | storage temperature                 |  | -65  | +150 | °C   |
| T <sub>i</sub>   | junction temperature                |  | -    | 150  | °C   |

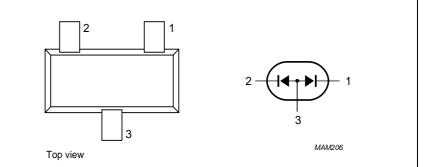
### Note

1. Device mounted on a FR4 printed-circuit board.

### Product data sheet

### PINNING

| PIN | DESCRIPTION  |  |
|-----|--------------|--|
| 1   | cathode      |  |
| 2   | cathode      |  |
| 3   | common anode |  |



**Marking code:** JZp = made in Hong Kong; JZt = made in Malaysia.

Fig.1 Simplified outline (SOT23) and symbol.

## **BAW156**

# BAW156

### ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$  unless otherwise specified.

| SYMBOL          | PARAMETER             | CONDITIONS  | TYP.  | MAX. | UNIT |
|-----------------|-----------------------|---|-------|------|------|
| Per diode       |                       | ·   |       |      |      |
| V <sub>F</sub>  | forward voltage       | see Fig.3   |       |      |      |
|                 |                       | I <sub>F</sub> = 1 mA   | _     | 900  | mV   |
|                 |                       | I <sub>F</sub> = 10 mA  | _     | 1000 | mV   |
|                 |                       | I <sub>F</sub> = 50 mA  | _     | 1100 | mV   |
|                 |                       | I <sub>F</sub> = 150 mA   | _     | 1250 | mV   |
| I <sub>R</sub>  | reverse current       | see Fig.5   |       |      |      |
|                 |                       | V <sub>R</sub> = 75 V   | 0.003 | 5    | nA   |
|                 |                       | V <sub>R</sub> = 75 V; T <sub>j</sub> = 150 °C  | 3     | 80   | nA   |
| C <sub>d</sub>  | diode capacitance     | $f = 1 \text{ MHz}; V_R = 0; \text{ see Fig.6}$   | 3     | -    | pF   |
| t <sub>rr</sub> | reverse recovery time | when switched from $I_F = 10$ mA to<br>$I_R = 10$ mA; $R_L = 100 \Omega$ ;<br>measured at $I_R = 1$ mA; see Fig.7 | 0.8   | 3    | μs   |

### THERMAL CHARACTERISTICS

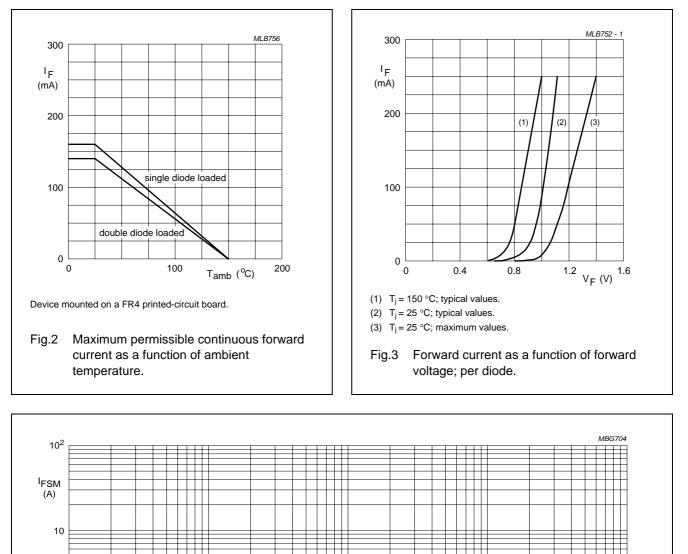
| SYMBOL               | PARAMETER                                     | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R <sub>th j-tp</sub> | thermal resistance from junction to tie-point |            | 360   | K/W  |
| R <sub>th j-a</sub>  | thermal resistance from junction to ambient   | note 1     | 500   | K/W  |

#### Note

1. Device mounted on a FR4 printed-circuit board.

## **BAW156**

### **GRAPHICAL DATA**



Based on square wave currents.

10

 $T_j = 25 \ ^\circ C$  prior to surge.

1

10<sup>-1</sup>

1

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

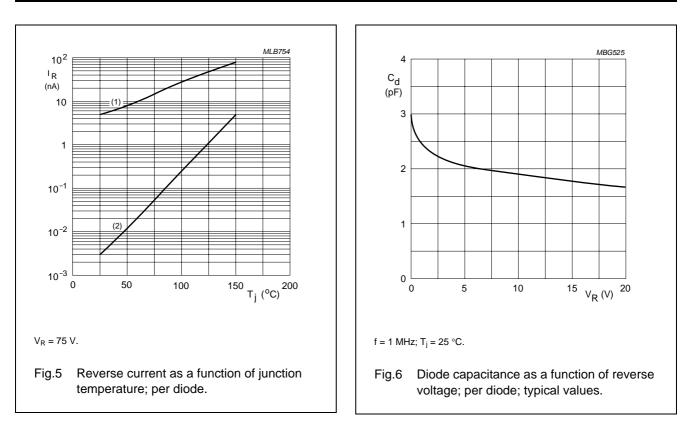
10<sup>2</sup>

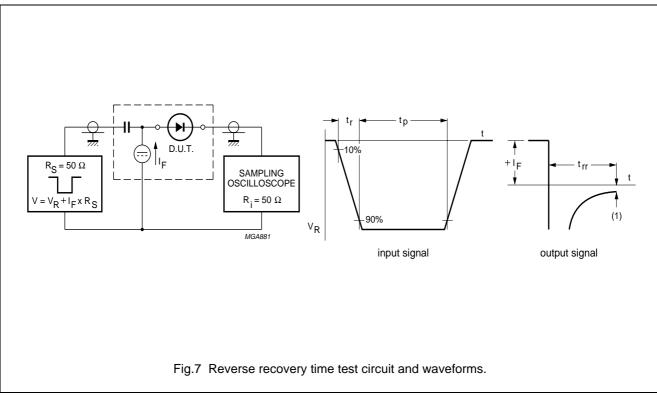
10<sup>3</sup>

10<sup>4</sup>

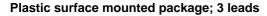
t<sub>p</sub> (μs)

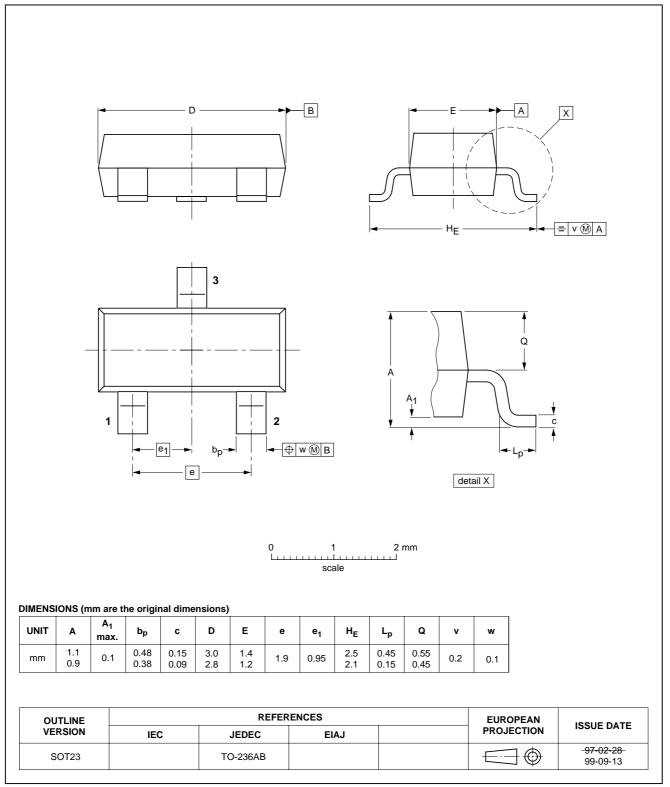
# BAW156





### PACKAGE OUTLINE





## **BAW156**

SOT23

**BAW156** 

#### DATA SHEET STATUS

| DOCUMENT<br>STATUS <sup>(1)</sup> | PRODUCT<br>STATUS <sup>(2)</sup> | DEFINITION  |
|-----------------------------------|----------------------------------|---|
| Objective data sheet              | Development                      | This document contains data from the objective specification for product development. |
| Preliminary data sheet            | Qualification                    | This document contains data from the preliminary specification.                       |
| Product data sheet                | Production                       | This document contains the product specification.                                     |

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#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

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